



Stud Diode

Rectifier Diode

SKN 26

SKR 26

Features

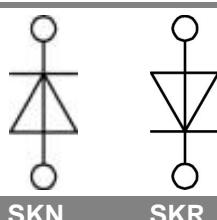
- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M6 (SKR 26 also 10 - 32 UNF)
- SKN: anode to stud, SKR: cathode to stud

Typical Applications

- All-purpose mean power rectifier diodes
- Cooling via metal plates or heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network: RC: 0,05 µF, 200 Ω ($P_R = 1 \text{ W}$), $R_P = 150 \text{ k}\Omega$ ($P_R = 4 \text{ W}$)

V_{RSM}	V_{RRM}	$I_{FRMS} = 40 \text{ A}$ (maximum value for continuous operation)	
V	V	$I_{FAV} = 25 \text{ A}$ (sin. 180 °; $T_c = 100 \text{ }^\circ\text{C}$)	
400	400	SKN 26/04	SKR 26/04
800	800	SKN 26/08	SKR 26/08
1200	1200	SKN 26/12	SKR 26/12
1400	1400	SKN 26/14	SKR 26/14
1600	1600	SKN 26/16	SKR 26/16

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 100 \text{ }^\circ\text{C}$	25	A
I_D	K 9; $T_a = 45 \text{ }^\circ\text{C}$; B2 / B6	20 / 29	A
	K 3; $T_a = 45 \text{ }^\circ\text{C}$; B2 / B6	35 / 50	A
I_{FSM}	$T_{vj} = 25 \text{ }^\circ\text{C}; 10 \text{ ms}$	375	A
	$T_{vj} = 180 \text{ }^\circ\text{C}; 10 \text{ ms}$	320	A
i^2t	$T_{vj} = 25 \text{ }^\circ\text{C}; 8,3 \dots 10 \text{ ms}$	700	A²s
	$T_{vj} = 180 \text{ }^\circ\text{C}; 8,3 \dots 10 \text{ ms}$	510	A²s
V_F	$T_{vj} = 25 \text{ }^\circ\text{C}; I_F = 60 \text{ A}$	max. 1,55	V
$V_{(TO)}$	$T_{vj} = 180 \text{ }^\circ\text{C}$	max. 0,85	V
r_T	$T_{vj} = 180 \text{ }^\circ\text{C}$	max. 11	mΩ
I_{RD}	$T_{vj} = 180 \text{ }^\circ\text{C}; V_{RD} = V_{RRM}$	max. 4	mA
Q_{rr}	$T_{vj} = 160 \text{ }^\circ\text{C}; -di_F/dt = 10 \text{ A}/\mu\text{s}$	20	µC
$R_{th(j-c)}$		2	K/W
$R_{th(c-s)}$		1	K/W
T_{vj}		- 40 ... + 180	°C
T_{stg}		- 55 ... + 180	°C
V_{isol}		-	V~
M_s	to heatsink	2,0	Nm
a		5 * 9,81	m/s²
m	approx.	8	g
Case		E 8	



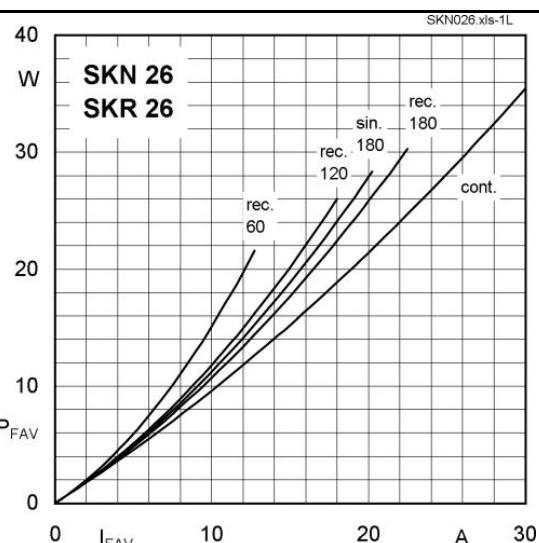


Fig. 1L Power dissipation vs. forward current

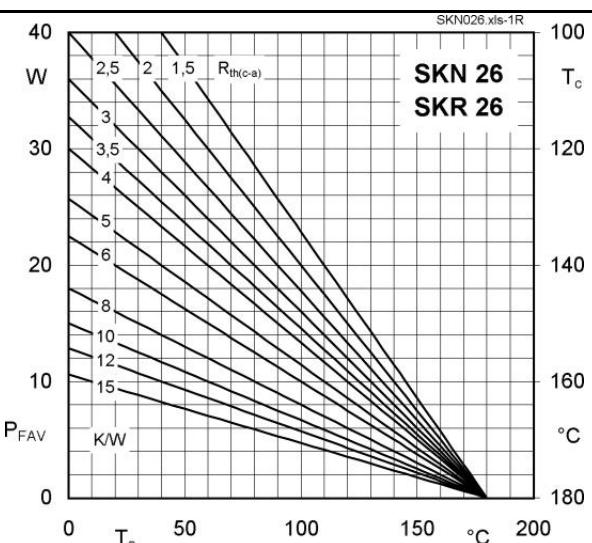


Fig. 1R Power dissipation vs. ambient temperature

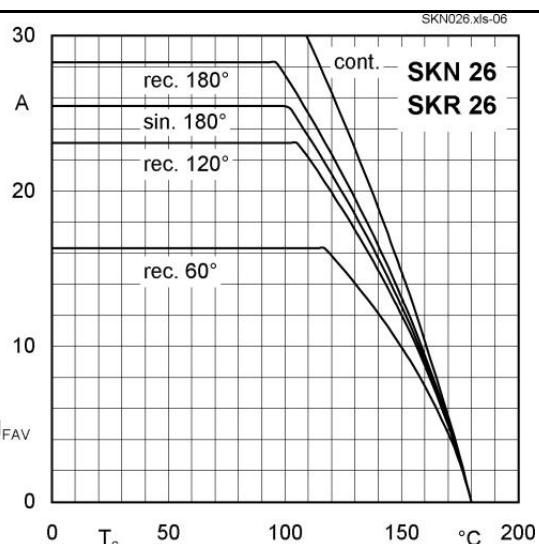


Fig. 2 Forward current vs. case temperature

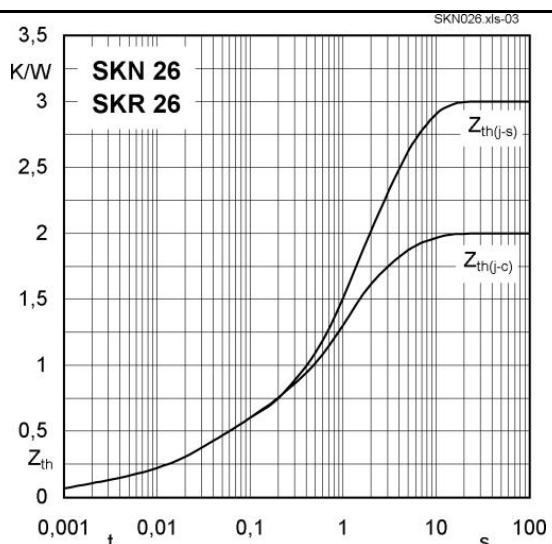


Fig. 4 Transient thermal impedance vs. time

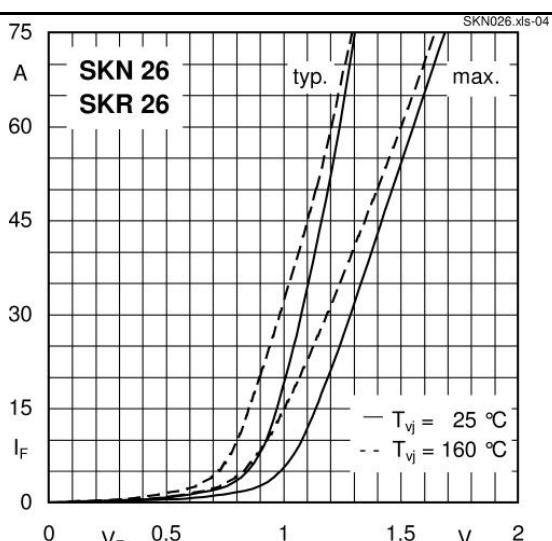


Fig. 5 Forward characteristics

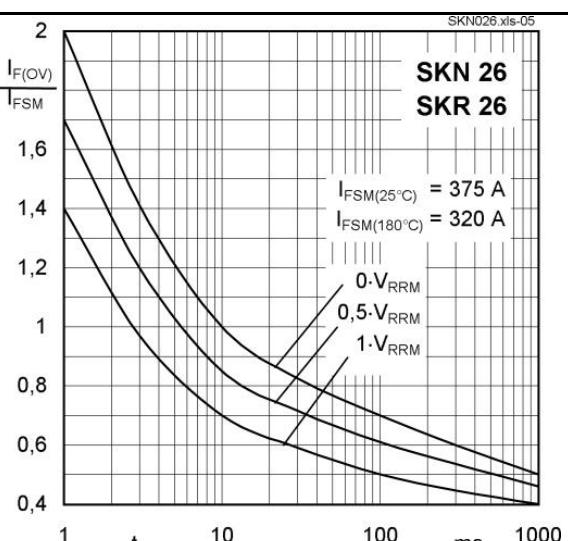
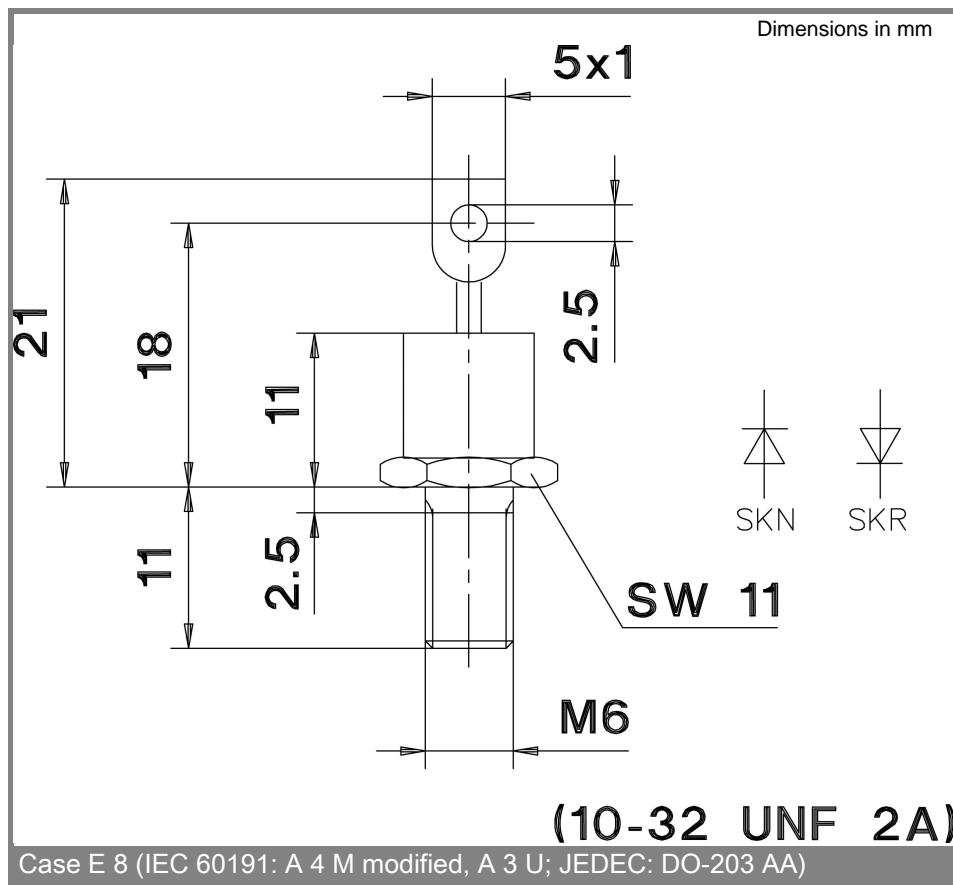


Fig. 6 Surge overload current vs. time



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